

# REF80 0.05ppm/°C のドリフト、変動が 1ppm 未満の安定性、温度制御型の埋め込みツェナーリファレンス

## 1 特長

- 最小の外部部品点数で 7.6V の超高精度リファレンス電圧
- 超低温度ドリフト: 0.05ppm/°C
- 優れた長期安定性: < 1ppm
- 温度安定インジケータ付き内蔵ヒーター
- 1/f ノイズ (0.1Hz~10Hz) : 0.16ppm<sub>pk-pk</sub>
- 入力電圧範囲: 10V~16.5V
- ヒーター電源範囲: 10V~42V
- 気密封止セラミック パッケージ (20 ピン LCCC)

## 2 アプリケーション

- [パラメトリック測定ユニット](#)
- [実験室およびフィールド向け計測機器](#)
- [高精度重量計](#)
- [バッテリーテスト機器](#)
- [デジタル マルチメータ](#)
- [ソース測定ユニット](#)
- [データアキュイジション](#)

## 3 概要

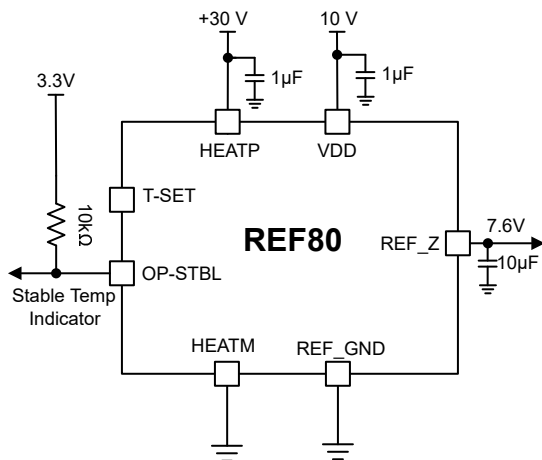
REF80 は、高集積、超低ドリフト、埋め込みツェナー型の高精度電圧リファレンスです。REF80 は、高精度の 7.6V リファレンスと内部ヒーターを組み合わせることで、0.05ppm/°C の非常に小さい温度ドリフトを実現します。内蔵ヒーターにより、ダイの内部温度を一定の設定ポイントに維持します。これにより、周囲温度の変動にかかわらず、リファレンス電圧を一定に維持できます。デバイスの内部温度は、設計の複雑さを除去するように事前プログラミングされています。これにより、設計サイクルが短縮され、簡単に起動でき、高コストの外付け高精度部品に依存する必要はありません。

REF80 ファミリーは、20 ピン LCCC パッケージで供給されます。LCCC パッケージは、キャリブレーションなしで長期間安定して動作することが必要とされるアプリケーションのために、1ppm という非常に低い長期ドリフト安定性仕様を実現できる気密封止セラミック パッケージです。このパッケージは、湿度の変化に対する耐性も非常に優れています。

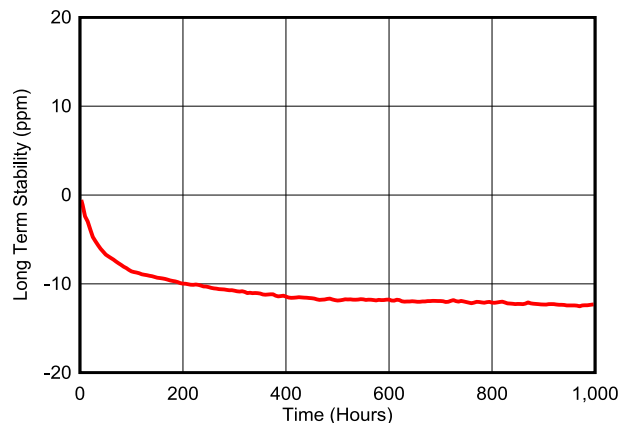
### 製品情報

部品番号	パッケージ <sup>(1)</sup>	本体サイズ (公称) <sup>(2)</sup>
REF80	LCCC (20)	8.89mm × 8.89 mm

- (1) 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。
- (2) パッケージサイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。



**REF80 回路図**  
(電源およびパッシブ要件を含む)



**リファレンス電圧ドリフトと時間との関係**



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#### 4 Device Comparison Table

PRODUCT	V <sub>REF_Z</sub>
REF80000B1NAJT	7.6V

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## 5 Pin Configuration and Functions

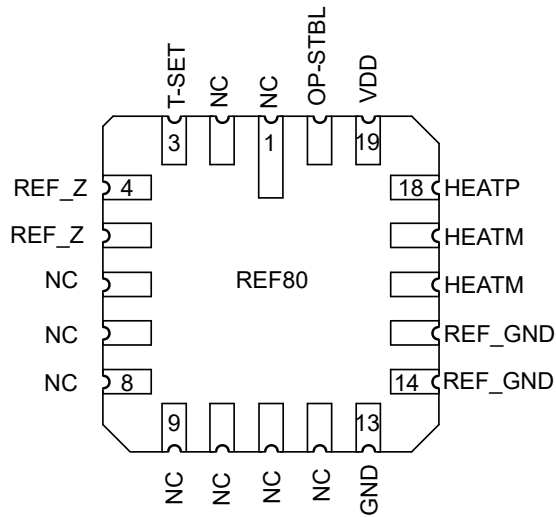


図 5-1. NAJ Package  
 20-Pin LCCC  
 Top View

表 5-1. Pin Functions

PIN		TYPE	DESCRIPTION
NAME	Number		
NC	1, 2, 6-12	No Connect	No connect pin. Leave this pin floating or connected to GND.
T-SET	3	Input	Connect resistor to adjust the heater temperature. Leave the pin floating to use factory programmed heater set point. Refer <a href="#">セクション 7.3.1</a> for more details.
REF_Z	4,5	Output	Reference voltage output. Connect an output capacitor between 10 $\mu$ F to 100 $\mu$ F for the best performance.
GND	13	GND	This pin should be shorted to REF_GND pin.
REF_GND	14, 15	Ground	Reference ground pin. This pin carries the current through the buried zener reference.
HEATM	16, 17	Power	Heater power supply negative connection.
HEATP	18	Power	Heater power supply positive connection.
VDD	19	Power	Power supply for buried zener core and buffer.
OP_STBL	20	Output	Active high output. Indicates the internal heater is stabilized at factory programmed temperature.

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## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range, all the voltages ratings are specified with respect to REF\_GND pin voltage (unless otherwise noted) <sup>(1)</sup>

		MIN	MAX	UNIT
Voltage	VDD, OP-STBL, NIC, NC	-0.3	18	V
Voltage	REF_Z	-0.3	10	V
Voltage	HEATP	-0.3	48	V
Voltage	HEATM	-42	0.3	V
Voltage	HEATP - HEATM	0	42	
Output short circuit current	I <sub>SC</sub>		30	mA
Operating temperature range	T <sub>A</sub>	-55	125	°C
Storage temperature range	T <sub>stg</sub>	-65	170	°C

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied. These are stress ratings only and functional operation of the device at these or any other conditions beyond those specified in the Electrical Characteristics Table is not implied.

### 6.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	±750	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.  
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Thermal Information

THERMAL METRIC <sup>(1)</sup>		REF80	UNIT
		NAJ (LCCC)	
		20 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	TBD	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	TBD	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	TBD	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	TBD	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	TBD	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 6.4 Recommended Operating Conditions

over operating free-air temperature range, all the voltages ratings are specified with respect to REF\_GND pin voltage (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Voltage	VDD (Input voltage)	10		16.5	V
	REF_Z	0		8	
	VHET Heater voltage, $V_{(HEATP - HEATM)}$	10		42	
	HEATP	0		42	
	HEATM	-42		0	
	OP-STBL (Output voltage stable indicator)	0		$V_{IN}$	
Current	OP-STBL Current (Output Logic Low, Active HIGH output)	0		5	mA
$T_A$	Operating temperature	0		70	°C

## 6.5 Electrical Characteristics

At VDD = 10V,  $V_{HEATER} = 30V$ ,  $C_{REF\_Z} = 10\mu F$ ,  $C_{VDD} = 1\mu F$ ,  $I_L = 0$  mA, minimum and maximum specifications across supported temperature range, typical specifications  $T_A = 25^\circ C$ ; unless otherwise noted

PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
<b>ACCURACY AND DRIFT</b>					
Output voltage	$T_A = 25^\circ C$		7.6		V
Output voltage accuracy	$T_A = 25^\circ C$	-50		50	mV
Output voltage temperature coefficient			0.05	0.2	ppm/°C
<b>HYSTERESIS AND LONG-TERM STABILITY</b>					
Long-term stability	0 to 336 Hours (14 days), $T_A = 25^\circ C$ , $T_{SET} = 115^\circ C$		10		ppm
	336 Hours to 1000 Hours, $T_A = 25^\circ C$ , $T_{SET} = 115^\circ C$		0.9		
$e_{np-p}$	Low frequency noise $f = 0.1\text{Hz to }10\text{Hz}$		0.16		ppm <sub>p-p</sub>
<b>NOISE</b>					
$e_n$	Output voltage noise $f = 10\text{Hz to }100\text{Hz}$ ,		0.6		$\mu V_{rms}$
<b>LINE AND LOAD REGULATION</b>					
$\frac{\Delta V_{REF\_Z}}{\Delta VDD}$	Line regulation VDD = 10V to 16.5V		4	10	ppm/V
<b>POWER SUPPLY</b>					
VDD	Input voltage	10		16.5	V
$V_{HEATER}$	Input voltage (HEATP - HEATM)	10		42	V
$I_{HEATER}$	Start up current		335		mA
	Quiescent current	$T_A = 25^\circ C$ , $T_{SET} = 115^\circ C$ , $V_{HEATER} = 10V$	75		
		$T_A = 25^\circ C$ , $T_{SET} = 115^\circ C$ , $V_{HEATER} = 42V$	18		
$I_{VDD}$	Quiescent current		15		mA
<b>TURNON TIME</b>					
Start-up	$V_{REF\_Z}$	REF_Z settled within $\pm 3\text{ppm}$	100		sec
	Heater Turn-on time	OP-STBL = 1	250		ms
<b>STABLE CAPACITANCE RANGE</b>					
	Input capacitor range		0.1		$\mu F$
	Output capacitor range <sup>(1)</sup>		10	100	$\mu F$

(1) ESR for the capacitor can range from 10 mΩ to 400 mΩ

## 6.6 Typical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $V_{IN} = 10\text{V}$ ,  $V_{HEATER} = 30\text{V}$ ,  $C_{REFZ} = 10\mu\text{F}$ ,  $C_{VDD} = 1\mu\text{F}$ , (unless otherwise noted)

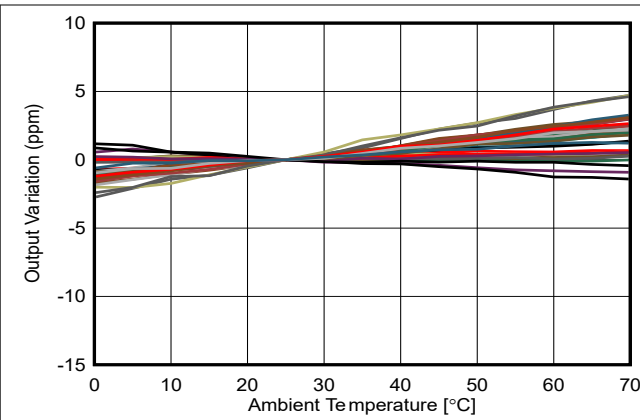


Figure 6-1. Output Voltage Vs Free-Air Temperature

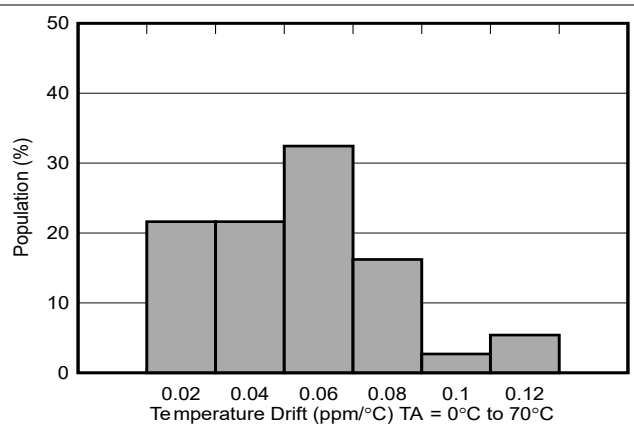


Figure 6-2. Temperature Drift Distribution

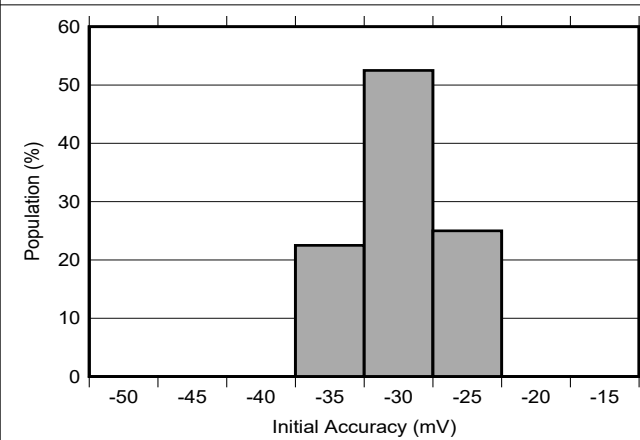


Figure 6-3. Accuracy Distribution

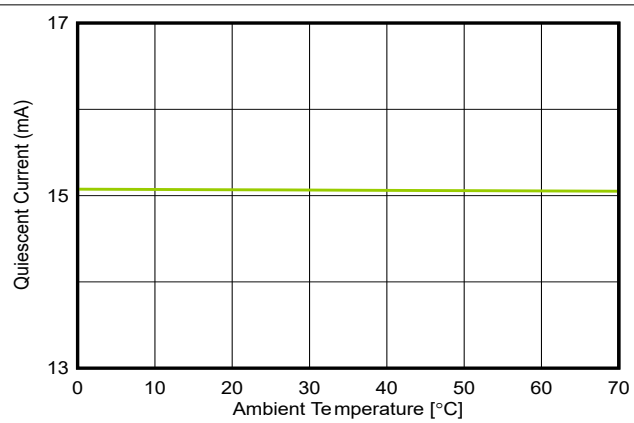


Figure 6-4. Supply Current ( $I_{VDD}$ ) vs Temperature

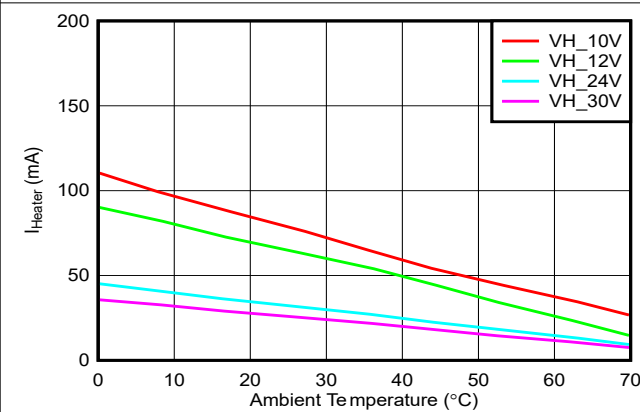


Figure 6-5. Heater Current ( $I_{Heater}$ ) vs Temperature

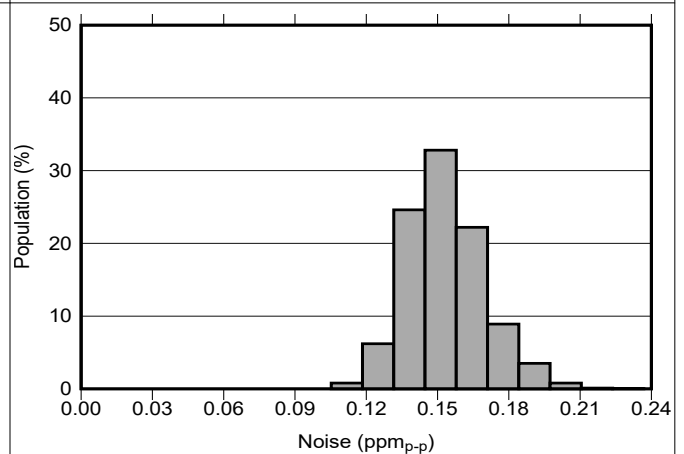


Figure 6-6. 0.1Hz to 10Hz Voltage Noise Distribution

### 6.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{IN} = 10\text{V}$ ,  $V_{HEATER} = 30\text{V}$ ,  $C_{REFZ} = 10\mu\text{F}$ ,  $C_{VDD} = 1\mu\text{F}$ , (unless otherwise noted)

ADVANCE INFORMATION

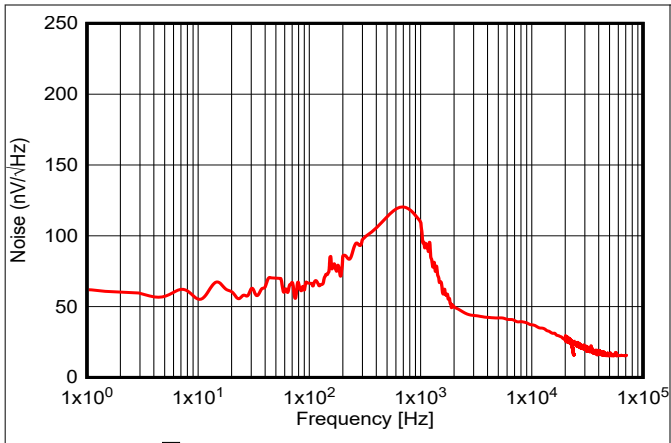


Figure 6-7. Noise Density vs Frequency

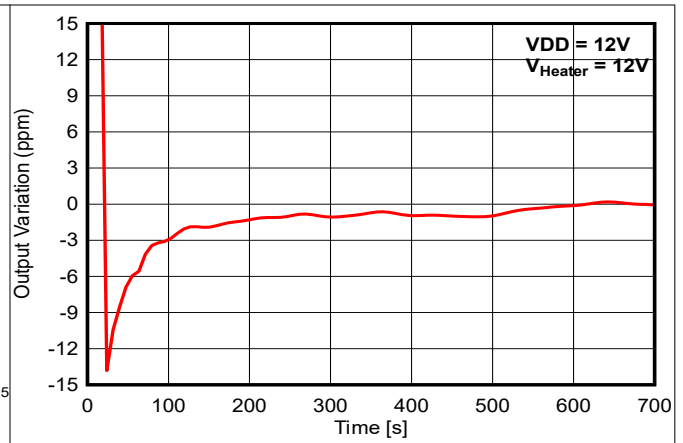


Figure 6-8. Startup Behavior

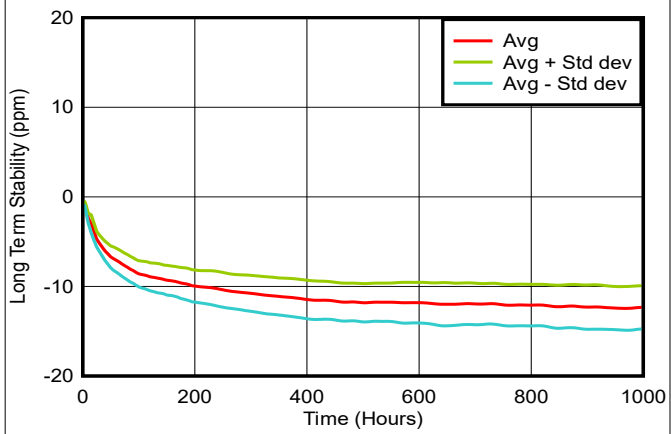


Figure 6-9. Long-Term Stability

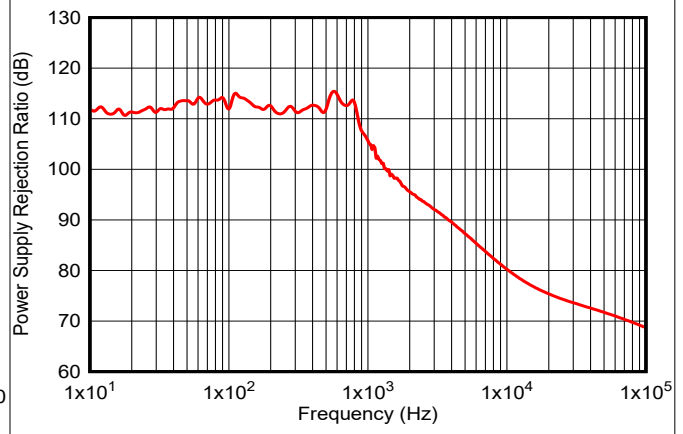


Figure 6-10. Power-Supply Rejection Ratio vs Frequency



## 7 Detailed Description

### 7.1 Overview

The REF80 is temperature controlled, buried zener voltage references specifically designed for excellent voltage stability over time and temperature. The [Figure 7-1](#) is the simplified block diagram of the REF80 showing the generation of voltage reference with buried zener and on chip heater control.

### 7.2 Functional Block Diagram

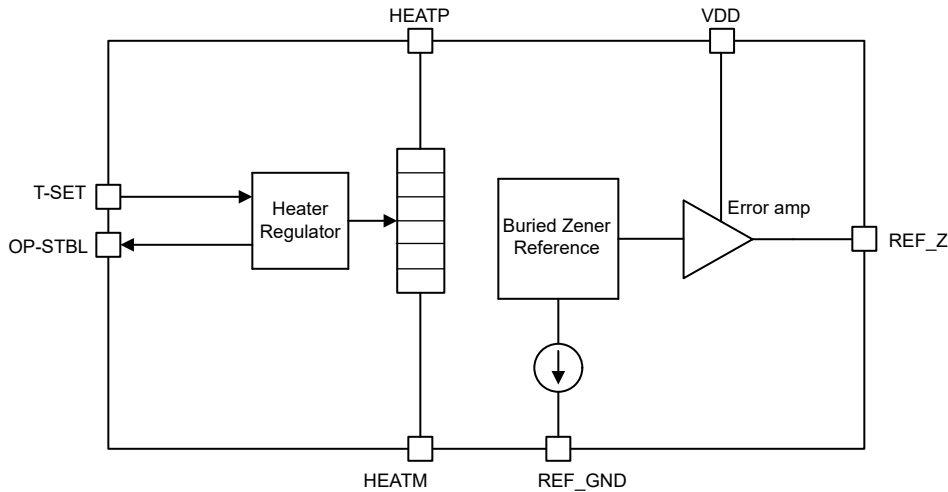


Figure 7-1. Functional Block Diagram for REF80

### 7.3 Feature Description

#### 7.3.1 Heater

REF80 has on chip heater which is factory programmed to  $T_{SET}$  temperature as per [T<sub>SET</sub> of Heater](#) to regulate the temperature of the die within  $\pm 1^\circ\text{C}$ , for the entire operating ambient temperature range. This allows REF80 to achieve ultra low temperature drift of 0.05ppm/  $^\circ\text{C}$ . Heater has dedicated supply pins HEATP and HEATM which run independent of VDD supply pin. The steady state power dissipation of the heater is directly proportional to the difference between ambient temperature  $T_A$  and  $T_{SET}$  as per [Equation 1](#). Heater current depends on (HEATP - HEATM) voltage. Heater takes high transient current at the time of start-up to heat up the device from ambient. REF80 has heater indicator pin OP\_STBL, which de-asserts when the heater reaches within  $\pm 0.1\%$  of  $T_{SET}$ .

#### T<sub>SET</sub> of Heater

Operating Temperature Range	T <sub>SET</sub>
0°C to 70°C	115°C

$$P_{HEATER} = \frac{T_{SET} - T_A}{R_{\theta JA}} - V_{DD} \times I_{VDD} \quad (1)$$

$V_{DD}$  is supply voltage for the chip and  $I_{VDD}$  is the supply current.

$R_{\theta JA}$  depends on board thickness and layout. The data sheet value of  $R_{\theta JA}$  is based on JEDEC standard board.

REF80 offers flexibility to decrease the heater temperature by putting a resistor on the T-SET pin as per [T-SET Pin Resistor VS Change in T<sub>SET</sub>](#) to save power and reduce the thermal noise for restricted ambient temperature applications.  $T_{SET}$  must be programmed to 45°C above the max ambient temperature to make sure that the heater is regulating the temperature properly. REF80 samples the value of the resistor at the time of startup and the value of  $T_{SET}$  is modified accordingly. Small drift in resistor value will not impact the  $T_{SET}$  temperature as T-SET pin samples discrete value.

**T-SET Pin Resistor VS Change in T<sub>SET</sub>**

Resistor on T-SET pin	Heater Temperature
0	T <sub>SET</sub>
130kΩ	T <sub>SET</sub> - 10°C
360kΩ	T <sub>SET</sub> - 20°C
800kΩ	T <sub>SET</sub> - 30°C
OPEN	T <sub>SET</sub>

### 7.3.2 Buried Zener Reference

The 7.6V reference output is generated with an ultra low noise buried zener diode which is biased at 15mA current. This buried zener exhibits extremely stable long term stability characteristics, which helps REF80 to achieve an accuracy of calibration grade instruments.

## 8 Parameter Measurement Information

### 8.1 Long-Term Stability

Buried zener references typically exhibit very stable long term stability and used as a ultra stable reference for internal calibration of the signal chain system. The long-term stability value is tested in a typical setup that reflects standard PCB board manufacturing practices for references with strain modulation structure around the device. The boards are made of standard FR4 material with 35µm of Copper.

Long term stability setup is designed with utmost care to minimize impact of thermocouple error, strain impact and mechanical vibration in long term stability measurement. The boards are maintained at 25°C in an air drift oven with heater temperature set to 115°C in powered on condition for long term stability measurement.

Typical long-term stability characteristic is expressed as a deviation over time. 図 8-1 shows the typical drift value for the REF80  $V_{REF\_Z}$  is 9ppm from 0 to 300 hours. Drift of REF80 quickly settles around 300 hours. Subsequent deviation is typically lower than 1ppm for the next 1000hr.

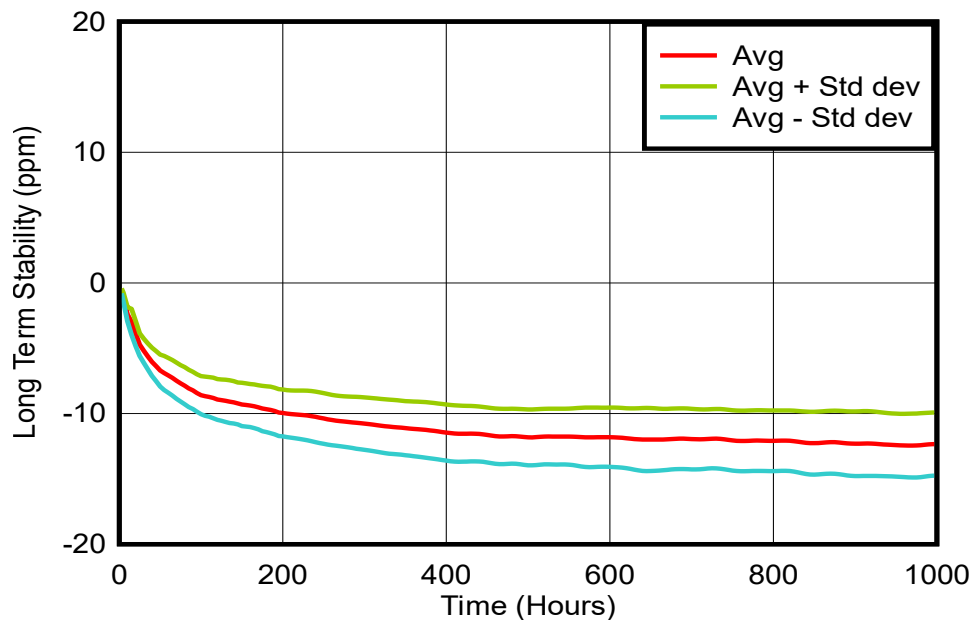


図 8-1. Long Term Stability ( $V_{REF\_Z}$ )

### 8.2 Temperature Drift

The REF80 has integrated on chip heater, which is factory programmed to  $T_{SET} = 105^{\circ}\text{C}$  temperature. Heater regulates the  $T_{SET}$  temperature to  $\pm 1^{\circ}\text{C}$  for entire operating temperature range. This results in 0.05ppm/ $^{\circ}\text{C}$  tempco for REF80.

The temperature coefficient is calculated using the box method in which a box is formed by the min/max variation for the nominal output voltage over the operating temperature range. REF80 has a maximum temperature coefficient of 0.2ppm/ $^{\circ}\text{C}$  for  $0^{\circ}\text{C}$  to  $70^{\circ}\text{C}$  temperature range. The box method specifies limits for the temperature error but does not specify the exact shape and slope of the device under test. See [SLYT183](#) for more information on the box method. The box method equation is shown in 式 2:

$$\text{Drift} = \left( \frac{V_{REF(\text{MAX})} - V_{REF(\text{MIN})}}{V_{REF(25^{\circ}\text{C})} \times \text{Temperature Range}} \right) \times 10^6 \quad (2)$$

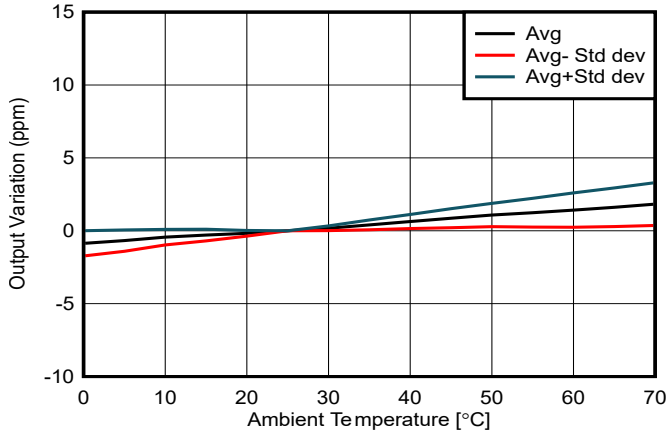


Figure 8-2. Output Voltage Vs Free-Air Temperature

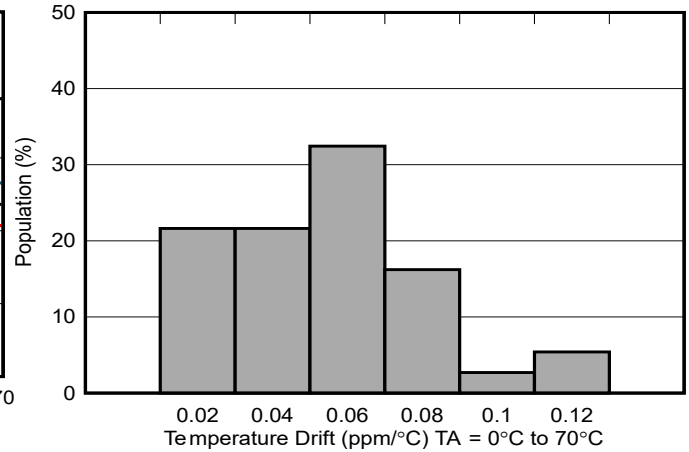


Figure 8-3. Temperature Drift Distribution

### 8.3 Noise Performance

#### 8.3.1 1/f Noise

1/f noise, also known as flicker noise, is dominant mostly in the lower frequency bands. Flicker noise affects the device output voltage which can affect the ENOB of the signal chain. REF80 data sheet specifies flicker noise for 0.1Hz to 10Hz frequency band where 1/f noise has maximum power. Flicker noise is measured by filtering the output from 0.1Hz to 10Hz. Since the 1/f noise is an extremely low value, the frequency of interest needs to be amplified and band-pass filtered as shown in Figure 8-4. 1/f noise must be tested in a Faraday cage enclosure to block environmental noise. Refer to application note [Techniques for Noise Measurements in Precision Series References](#) for more detail on noise measurement for precision series references.

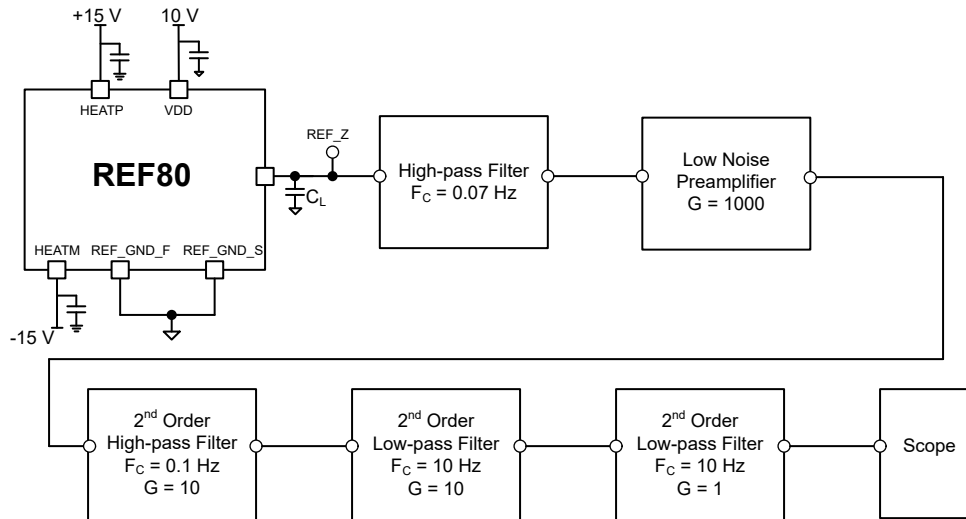


Figure 8-4. 1/f Noise Test Setup

Typical 1/f noise (0.1Hz to 10Hz) distribution can be seen in Figure 8-5.

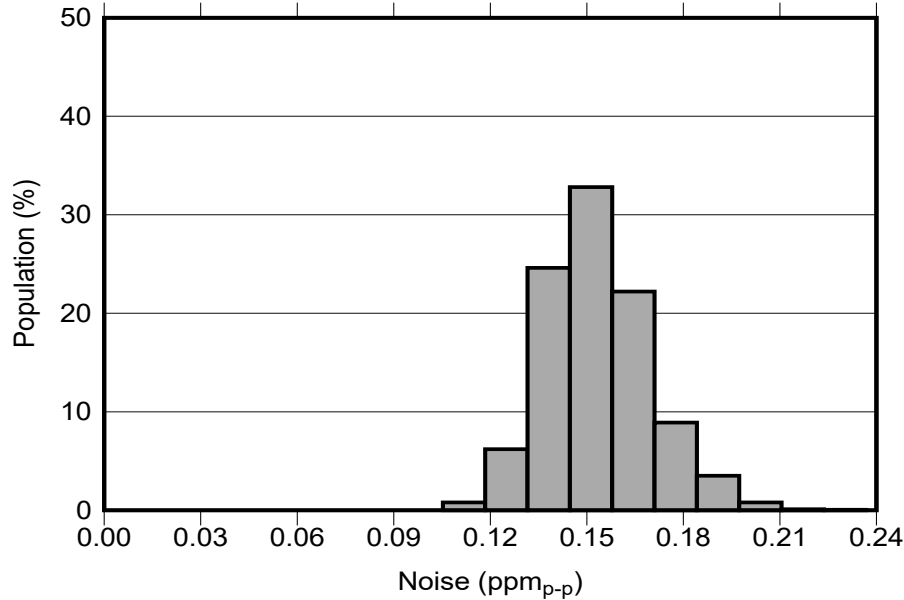


図 8-5. 0.1Hz to 10Hz Voltage Noise Distribution

The 1/f noise is in such a low frequency range that it is not practical to filter out which makes it a key parameter for ultra-low noise measurements. Noise sensitive designs must use the lowest 1/f noise for the highest precision measurements. 図 8-6 shows the effect of 1/f noise over 10s.

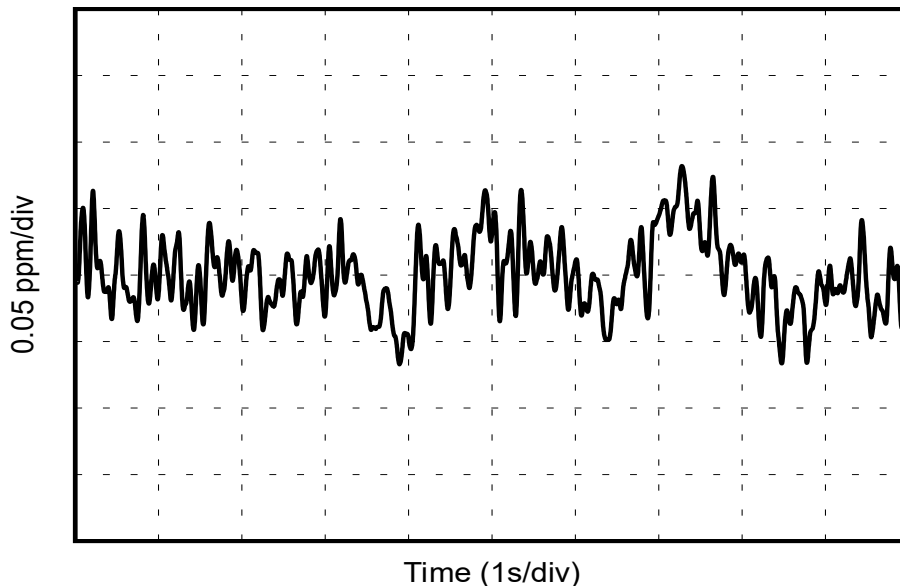


図 8-6. 0.1Hz to 10Hz Voltage Noise

### 8.3.2 Broadband Noise

Broadband noise is a noise that appears at higher frequency compared to 1/f noise. The broadband noise is dominated by white noise as shown in 図 8-8 . The broadband noise is measured by high-pass filtering the output of the REF80 and measuring the result on a spectrum analyzer as shown in 図 8-7. The DC component of the REF80 is removed by using a high-pass filter and then amplified. When measuring broadband noise, it is not necessary to have high gain to achieve maximum bandwidth.

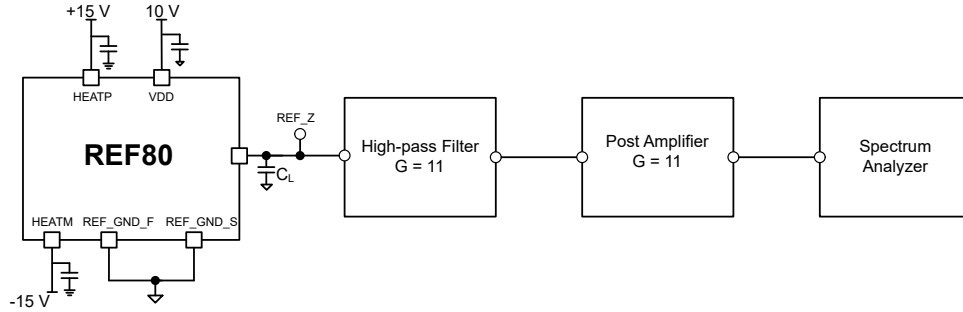


図 8-7. Broadband Noise Test Setup

For noise sensitive designs, a low-pass filter can be used to reduce broadband noise output noise levels by removing the high frequency components. When designing a low-pass filter special care must be taken to make sure the output impedance of the filter does not degrade ac performance. This can occur in RC low-pass filters where a large series resistance can impact the load transients due to output current fluctuations.

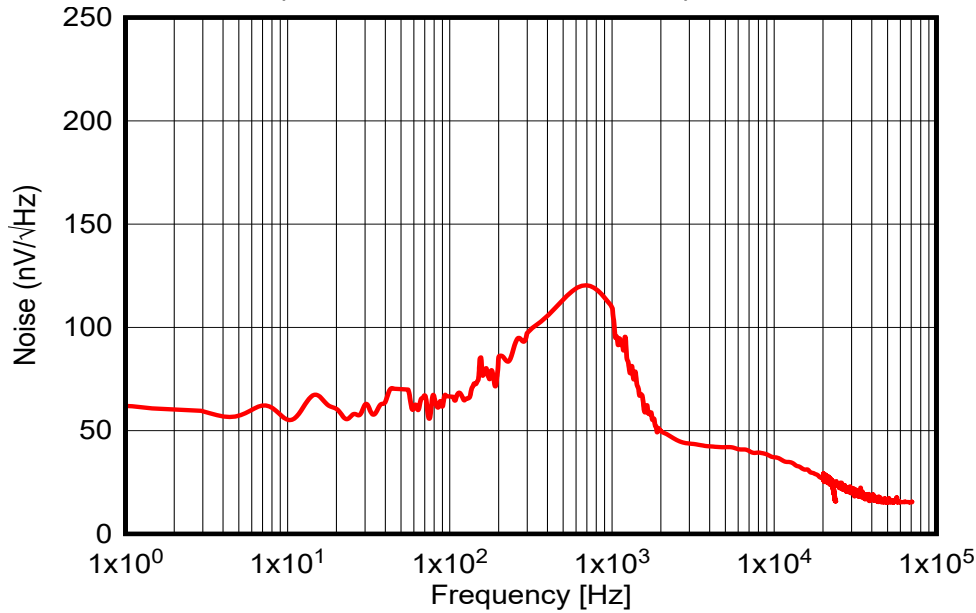


図 8-8. Noise Performance 10Hz to 10kHz

## 9 Application and Implementation

### 注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 9.1 Application Information

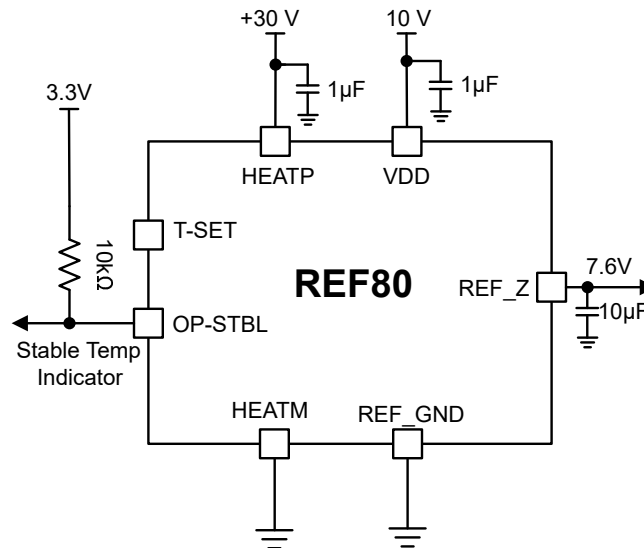
Basic applications convert the REFZ output to calibration signal or connect it to  $\leq 5V$  signal for precision data converter. The table below shows the typical applications of REF80 and its companion data converters.

APPLICATION	DATA CONVERTER
Test & Measurement	<a href="#">DAC11001B</a>

### 9.2 Typical Applications

#### 9.2.1 Typical Application: Basic Voltage Reference Connection

The circuit shown in [図 9-1](#) shows the basic configuration for the REF80 references. Connect bypass capacitors according to the guidelines in [セクション 9.4.1](#).



**図 9-1. Basic Reference Connection**

### 9.2.1.1 Design Requirements

A detailed design procedure is based on a design example. For this design example, use the parameters listed in 表 9-1 as the input parameters.

表 9-1. Design Example Parameters

DESIGN PARAMETER	VALUE
Input voltage $V_{DD}$	10V
Heater Voltage $V_{HEATER}$ (HEATP - HEATM)	30V
Supply decoupling capacitor	1 $\mu$ F
Heater supply decoupling capacitor	1 $\mu$ F
OP-STBL pull-up resistor	10k $\Omega$
OP-STBL pull-up supply	3V

### 9.2.1.2 Detailed Design Procedure

#### 9.2.1.2.1 Application Curve

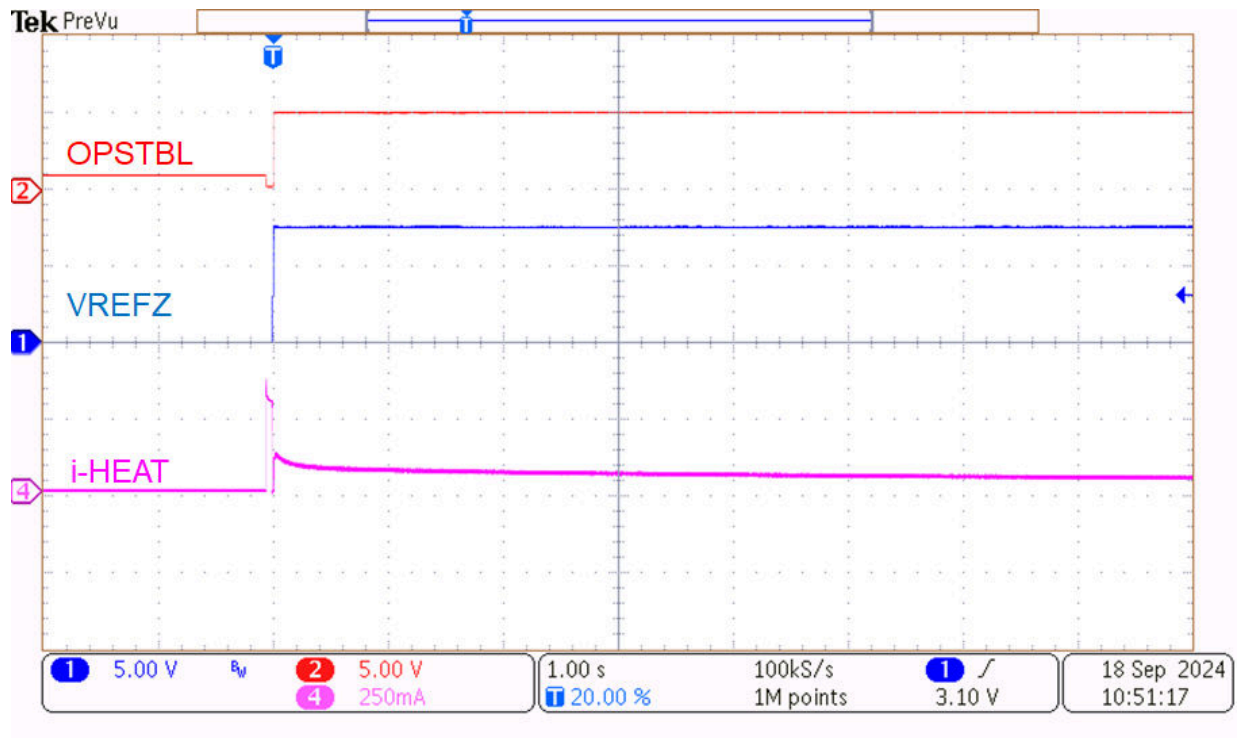


図 9-2. REF80 Startup Behavior

ADVANCE INFORMATION



## 9.2.2 Typical Application Circuits

### 9.2.2.1 Precision Voltage Divider Connection

Precision data converters typically require voltage reference which is less than or equal to 5V. REF80 requires a precision resistor divider followed by low noise buffer to generate reference voltage for data converters as shown in [Figure 9-3](#).

The selection of resistor depends on the current capability (< 1mA is preferred) and noise requirement. Minimum value of resistors are decided by the output current as per [Equation 4](#).

$$R1 + R2 \geq 7.6k\Omega \quad (3)$$

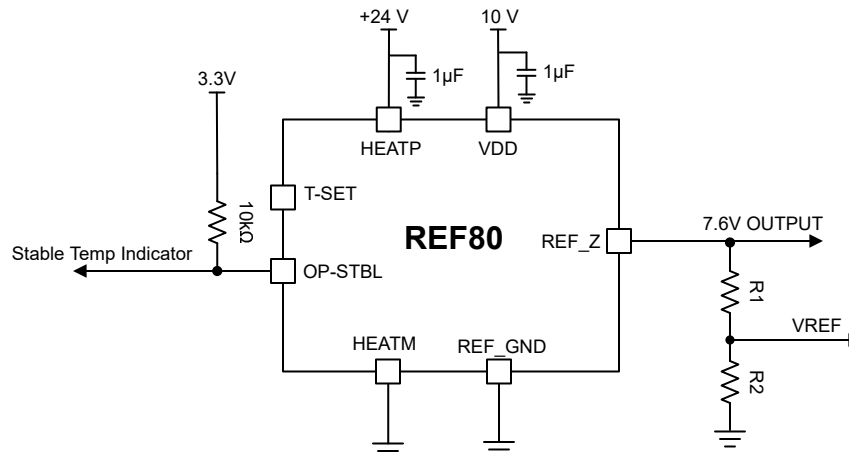
Maximum value of the resistors are decided by the noise consideration. Thermal noise of the resistors (parallel equivalent) is added as per [Equation 5](#)

$$V_{REF_{Noise}} = \sqrt{\left(\left(\frac{R2}{R1 + R2} \times REF\_Z_{Noise}\right)^2 + (R1 || R2)_{Thermal\ Noise}\right)^2} \quad (4)$$

Where

- $V_{REF_{Noise}}$  = Reference noise requirement in desired frequency band
- $REF\_Z_{Noise}$  = REF80 noise in desired frequency band
- $R1 || R2_{Thermal\ noise}$  = Thermal noise of parallel equivalent of R1 and R2 resistor

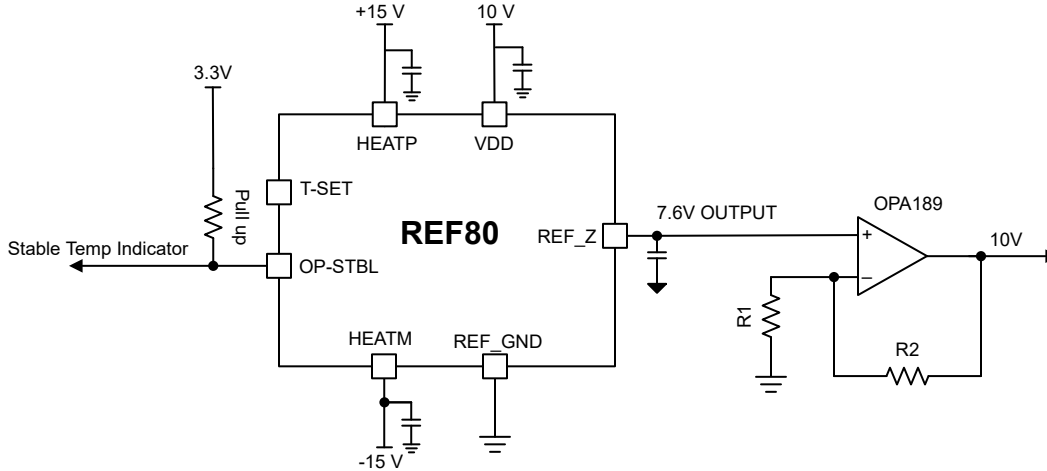
R1 and R2 must be precision foil resistors with matched temperature drift for best performance.



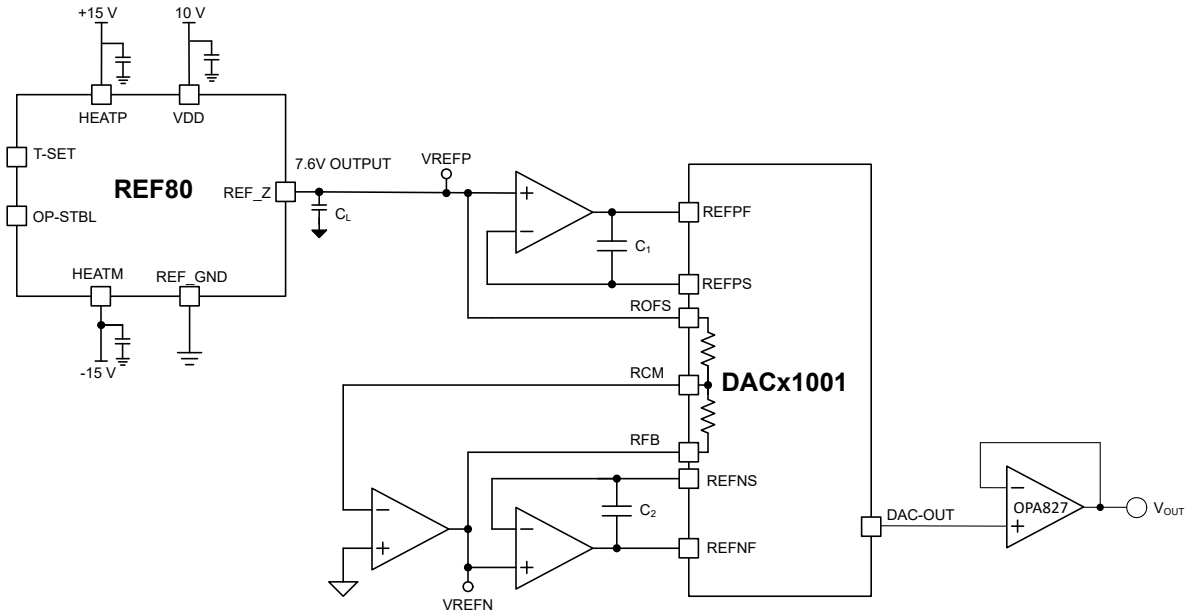
**Figure 9-3. Precision Resistor Divider Connection**

### 9.2.2.2 Calibration Signal

Ultra low long term stability and temperature drift makes REF80 an excellent choice for metrology grade calibration signal generation.



9-4. 10V Precision Signal With Amplifier And Precision Resistors



9-5. Precision Signal With DACx1001

ADVANCE INFORMATION

## 9.3 Power Supply Recommendation

The buried zener reference requires a stable power supply of 10V to 16.5V for stable operation of the REF\_Z pin. Potential difference between HEATP and HEATM pin must be 10V to 42V. HEATP must always be connected to a positive supply or ground. HEAM must always be connected to a negative supply or ground. The heater supply must be able to provide high inrush current for fast start-up of the device. TI recommends a supply bypass capacitor ranging between 0.1 $\mu$ F to 10 $\mu$ F.

## 9.4 Layout

### 9.4.1 Layout Guidelines

Layout Example illustrates an example of a PCB layout for a data acquisition system using the REF80. Some key considerations are:

- **Noise performance**
  - Connect low-ESR, 0.1 $\mu$ F ceramic bypass capacitors at  $V_{DD}$ , HEATM and HEATP of the REF80.
  - Connect 10 $\mu$ F to 100 $\mu$ F class 1 capacitor at REFZ of the REF80.
  - Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when absolutely necessary.
- **Thermal performance**
  - The layout must minimize the heat dissipation to maintain good thermal resistance for REF80.
  - Use minimum copper to route  $V_{DD}$ , REF\_Z, REF\_GND signal.
  - Use copper as per current requirement for HEATP and HEATM pin.
  - Avoid direct copper pours underneath the package.
- **Seebeck effect**
  - Avoid multiple metal-metal junction to minimize Seebeck effect.
- **Long term stability performance**
  - Provide strain relief directly to pins as shown in the Layout Example.
  - Provide cuts near to the pin, perpendicular to the pins and corners.
  - Avoid single point strain accumulation.

## 10 Device and Documentation Support

### 10.1 Documentation Support

#### 10.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [Voltage Reference Design Tips For Data Converters](#)
- Texas Instruments, [Voltage Reference Selection Basics](#)

### 10.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[www.tij.co.jp](http://www.tij.co.jp) のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

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[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

## 11 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

DATE	REVISION	NOTES
September 2024	*	Initial Release

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
PREF80000B1NAJT	ACTIVE	LCCC	NAJ	20	250	TBD	Call TI	Call TI	-55 to 125		Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

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**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

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**OBSELETE:** TI has discontinued the production of the device.

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(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

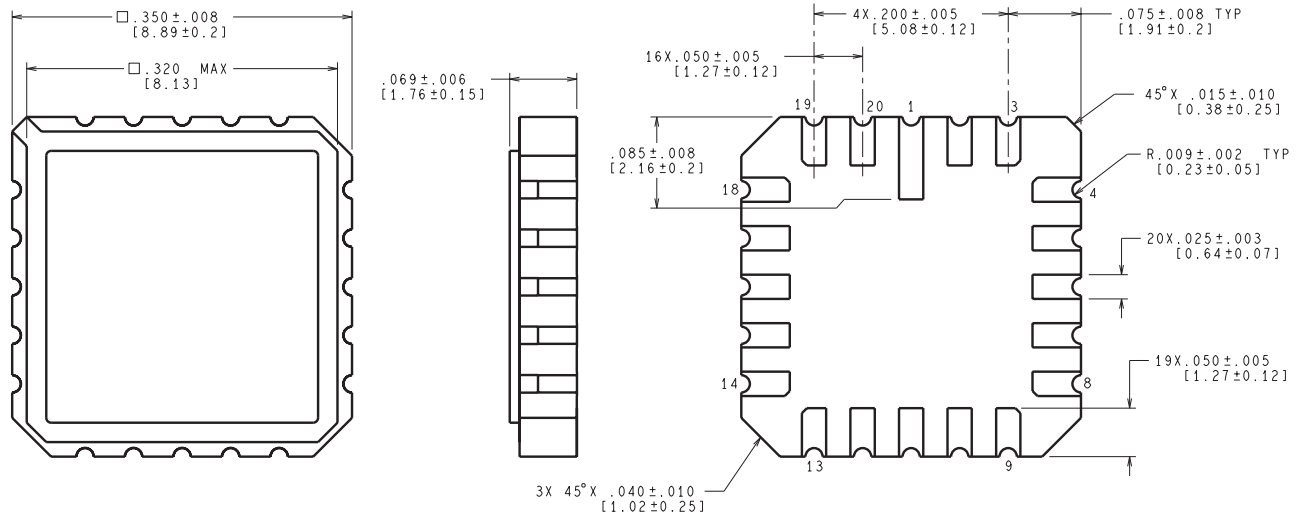
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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